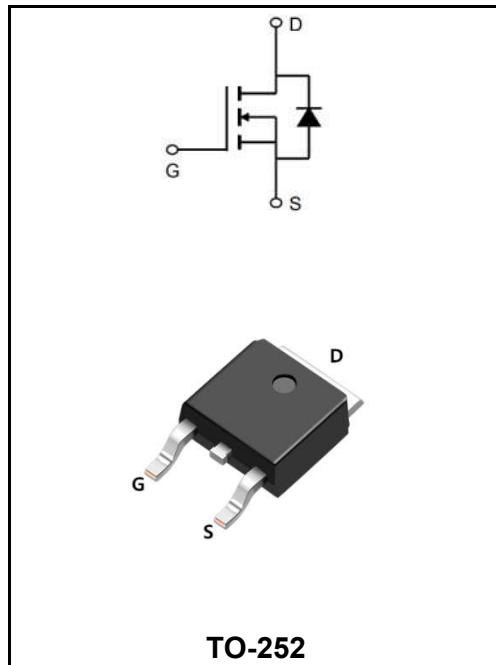


**40V N-CHANNEL ENHANCEMENT MODE MOSFET**
**MAIN CHARACTERISTICS**

$I_D$	50A
$V_{DSS}$	40V
$R_{DS(on)-typ}(@V_{GS}=10V)$	< 17mΩ (Type: 13.5 mΩ)


**Application**

- Battery protection
- Load switch
- Uninterruptible power supply

**Product Specification Classification**

Part Number	Package	Marking	Pack
YFW50N04AD	TO-252	YFW 50N04AD XXXXX	2500PCS/Tape

**Maximum Ratings at  $T_c=25^\circ\text{C}$  unless otherwise specified**

Characteristics	Symbols	Value	Units
Drain-Source Voltage	$V_{DS}$	40	V
Gate - Source Voltage	$V_{GS}$	$\pm 20$	V
Continuous Drain Current, $V_{GS} @ 10V^1$ @ $T_c=25^\circ\text{C}$	$I_D$	50	A
Continuous Drain Current, $V_{GS} @ 10V^1$ @ $T_c=100^\circ\text{C}$	$I_D$	23	A
Pulsed Drain Current <sup>2</sup>	$I_{DM}$	85	A
Single Pulse Avalanche Energy <sup>3</sup>	$E_{AS}$	31.3	mJ
Avalanche Current	$I_{AS}$	25	A
Total Power Dissipation <sup>4</sup> @ $T_c=25^\circ\text{C}$	$P_D$	31.3	W
Total Power Dissipation <sup>4</sup> @ $T_A=25^\circ\text{C}$	$P_D$	2	W
Storage Temperature Range	$T_{STG}$	-55 to +150	°C
Operating Junction Temperature Range	$T_J$	-55 to +150	°C
Thermal Resistance, Junction-to-Ambient <sup>1</sup>	$R_{\theta JA}$	65	°C/W
Thermal Resistance Junction-Case <sup>1</sup>	$R_{\theta JC}$	3	°C/W

**Maximum Ratings at Tc=25°C unless otherwise specified**

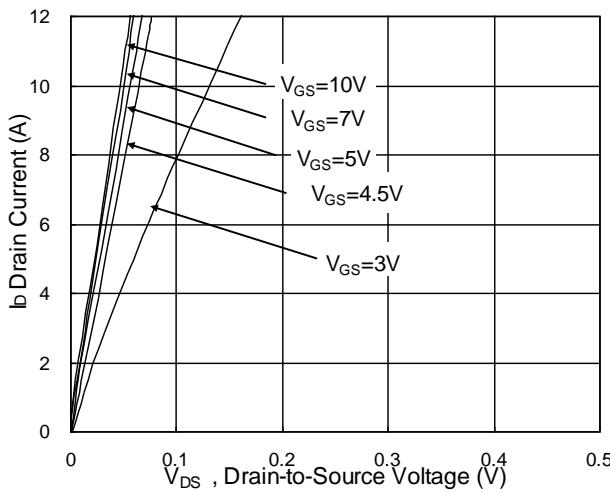
Characteristics	Test Condition	Symbols	Min	Typ	Max	Units
Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V, I <sub>D</sub> =250uA	BV <sub>DSS</sub>	40	-	-	V
BVDSS Temperature Coefficient	Reference to 25°C , I <sub>D</sub> =1mA	ΔBV <sub>DSS/ΔTJ</sub>	-	0.032	-	V/°C
Static Drain-Source On-Resistance <sup>2</sup>	V <sub>GS</sub> =10V, I <sub>D</sub> =15A	R <sub>DS(ON)</sub>	-	13.5	17	mΩ
	V <sub>GS</sub> =4.5V, I <sub>D</sub> =10A		-	18.4	24	
Gate -Threshold Voltage	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =250uA	V <sub>GS(th)</sub>	1.2	1.6	2.5	V
V <sub>GS(th)</sub> Temperature Coefficient		ΔV <sub>GS(th)</sub>	-	-4.8	-	mV/°C
Drain -Source Leakage Current	V <sub>DS</sub> =32V , V <sub>GS</sub> =0V , T <sub>J</sub> =25°C	I <sub>DSS</sub>	-	-	1	μA
	V <sub>DS</sub> =32V , V <sub>GS</sub> =0V , T <sub>J</sub> =55°C		-	-	5	
Gate-Source Leakage Current	V <sub>GS</sub> =±20V, V <sub>DS</sub> =0V	I <sub>GSS</sub>	-	-	±100	nA
Forward Transconductance	V <sub>DS</sub> =5V, I <sub>D</sub> =15A	g <sub>FS</sub>	-	34	-	S
Gate Resistance	V <sub>DS</sub> =0V , V <sub>GS</sub> =0V , f=1MHz	R <sub>g</sub>	-	2.1	-	Ω
Total Gate Charge(4.5V)	V <sub>DS</sub> =32V V <sub>GS</sub> =4.5V I <sub>D</sub> =15A	Q <sub>g</sub>	-	10	-	nC
Gate-Source Charge		Q <sub>gs</sub>	-	2.55	-	
Gate-Drain Charge		Q <sub>gd</sub>	-	4.8	-	
Turn-on delay time	V <sub>DD</sub> =20V V <sub>GS</sub> =10V R <sub>G</sub> =3.3 I <sub>D</sub> =15A	t <sub>d(on)</sub>	-	2.8	-	ns
Rise Time		T <sub>r</sub>	-	12.8	-	
Turn-Off Delay Time		t <sub>d(OFF)</sub>	-	21.2	-	
Fall Time		t <sub>f</sub>	-	6.4	-	
Input Capacitance	V <sub>DS</sub> =15V V <sub>GS</sub> =0V f=1.0MHz	C <sub>iss</sub>	-	1013	-	pF
Output Capacitance		C <sub>oss</sub>	-	107	-	
Reverse Transfer Capacitance		C <sub>rss</sub>	-	76	-	
Continuous Source Current <sup>1,5</sup>	V <sub>G</sub> =V <sub>D</sub> =0V , Force Current	I <sub>s</sub>	-	-	40	A
Pulsed Source Current <sup>2,5</sup>		I <sub>SM</sub>	-	-	85	A
Diode Forward Voltage <sup>2</sup>	V <sub>GS</sub> =0V , I <sub>s</sub> =1A , T <sub>J</sub> =25°C	V <sub>SD</sub>	-	-	1.2	V
Reverse Recovery Time	I <sub>F</sub> =15A , dI/dt=100A/μs , T <sub>J</sub> =25°C	t <sub>rr</sub>	-	10	-	ns
Reverse Recovery Charge		Q <sub>rr</sub>	-	3.1	-	nC

Note :

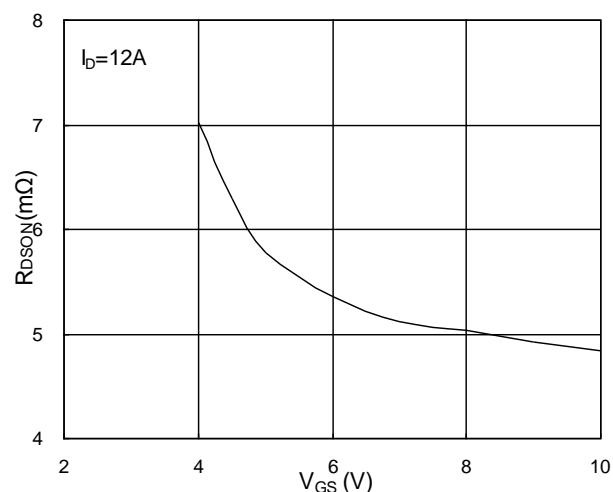
- 1 .The data tested by surface mounted on a 1 inch<sup>2</sup> FR-4 board with 2OZ copper.
- 2.The data tested by pulsed , pulse width ≤ 300us , duty cycle ≤ 2%
- 3 .The EAS data shows Max. rating . The test condition is VDD=25V,VGS=10V,L=0.1mH,IAS=25A
- 4.The power dissipation is limited by 150°C junction temperature
- 5.The data is theoretically the same as ID and IDM , in real applications , should be limited by total power dissipation.

## Ratings and Characteristic Curves

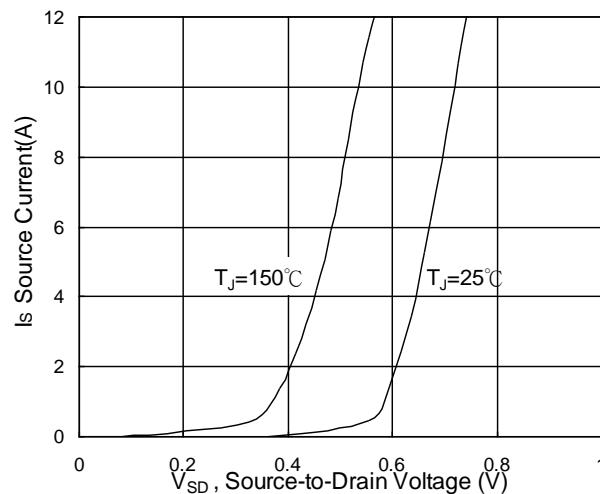
### Typical Characteristics



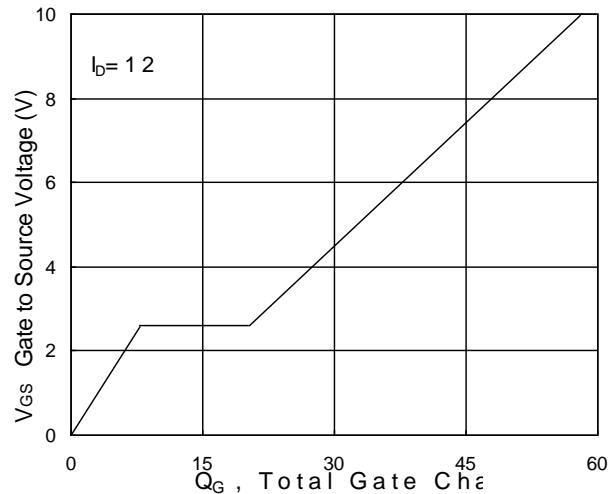
**Fig.1 Typical Output Characteristics**



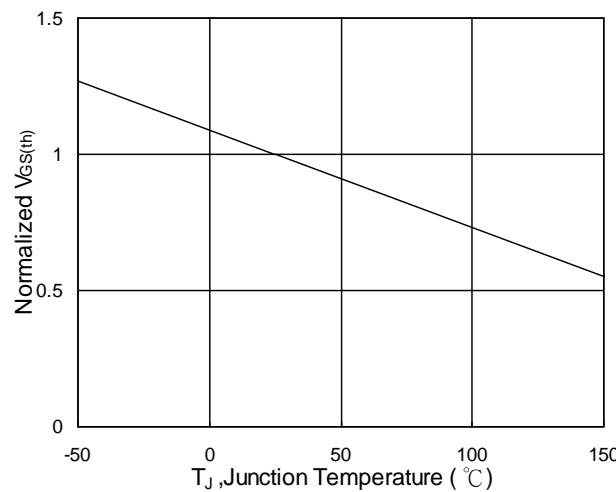
**Fig.2 On-Resistance vs. G-S Voltage**



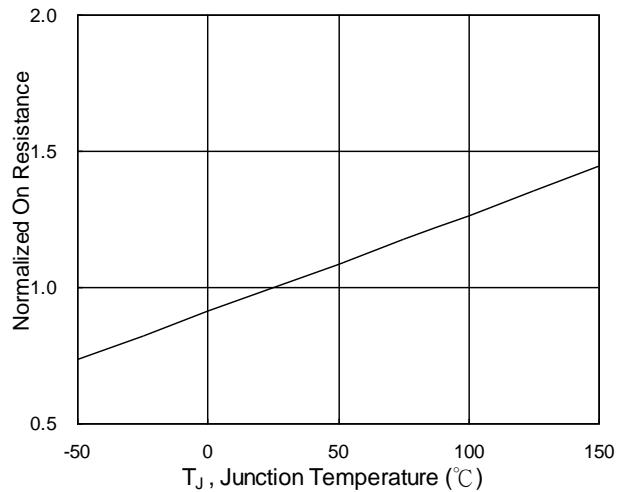
**Fig.3 Forward Characteristics Of Reverse**



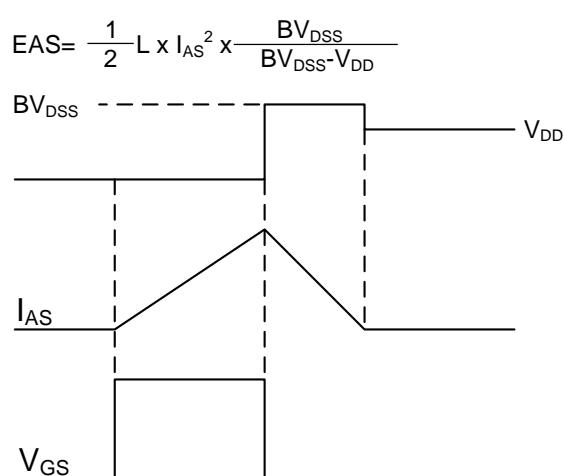
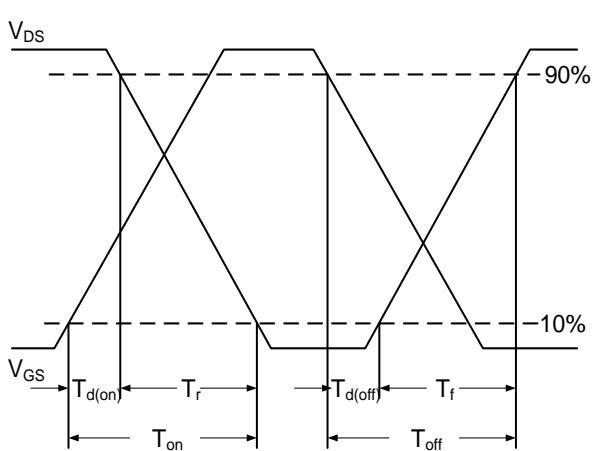
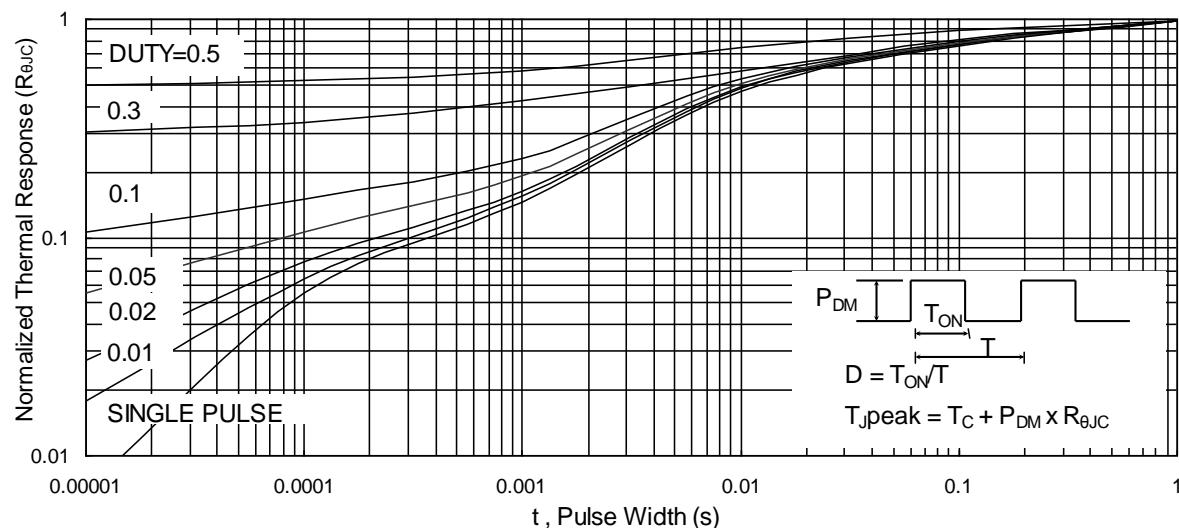
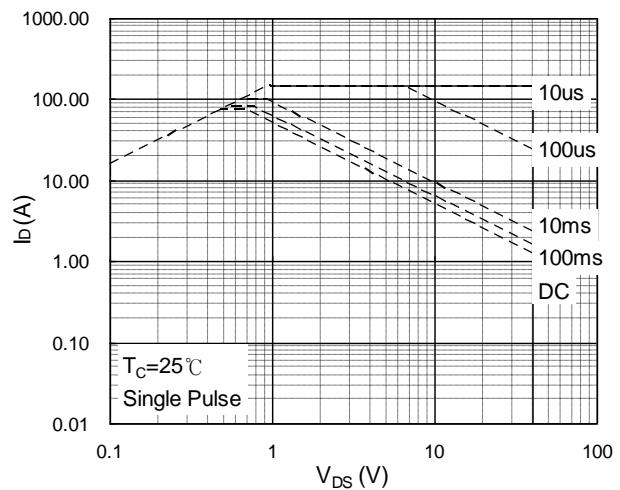
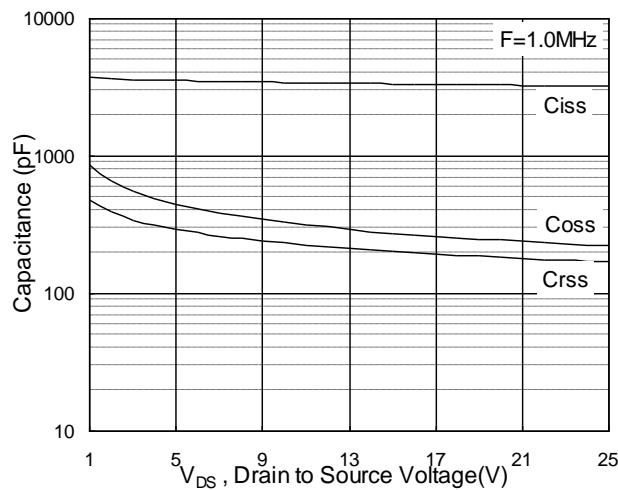
**Fig.4 Gate-Charge Characteristics**



**Fig.5 Normalized  $V_{GS(th)}$  vs.  $T_J$**

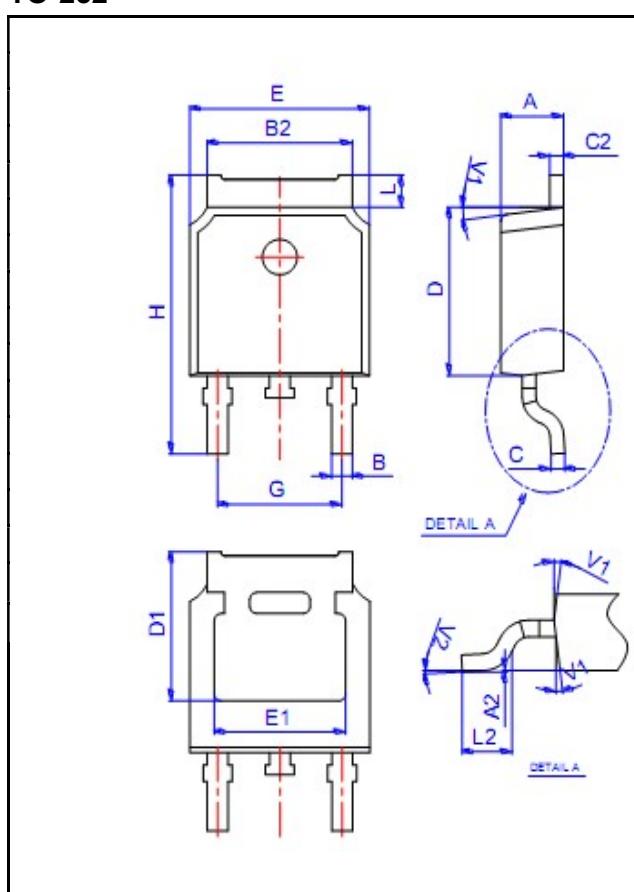


**Fig.6 Normalized  $R_{DS(on)}$  vs.  $T_J$**

**Ratings and Characteristic Curves**


**Package Outline Dimensions Millimeters**

**TO-252**



Dim.	Min.	Typ.	Max.
A	2.10	-	2.50
A2	0	-	0.10
B	0.66	-	0.86
B2	5.18	-	5.48
C	0.40	-	0.60
C2	0.44	-	0.58
D	5.90	-	6.30
D1	5.30REF		
E	6.40	-	6.80
E1	4.63	-	-
G	4.47	-	4.67
H	9.50	-	10.70
L	1.09	-	1.21
L2	1.35	-	1.65
V1	-	7°	-
V2	0°	-	6°

All Dimensions in millimeter